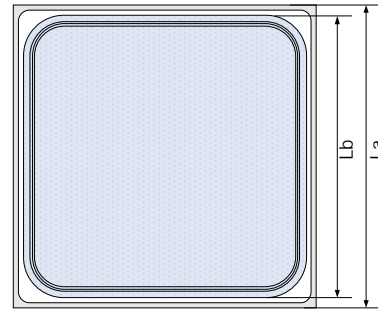


2SB124100ML SCHOTTKY BARRIER DIODE CHIPS
DESCRIPTION

- Ø 2SB124100ML is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits.;
- Ø Chip Size:1240 μ m X 1240 μ m;
- Ø Chip Thickness: 280 \pm 20 μ m;


Chip Topography and Dimensions

 La: Chip Size: 1240 μ m;

 Lb: Pad Size: 1100 μ m;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB124100MLYY	For axial leads package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	100	V
Average Forward Rectified Current	IFAV	2	A
Peak Forward Surge Current@8.3ms	IFSM	50	A
Maximum Operation Junction Temperature	TJ	125	$^{\circ}$ C
Storage Temperature Range	TSTG	-40~125	$^{\circ}$ C

ELECTRICAL CHARACTERISTICS (T_{amb}=25 $^{\circ}$ C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=1mA	100	--	V
Forward Voltage	VF	IF=2A	--	0.85	V
Reverse Current	IR	VR=100V	--	1	mA